Date: 2013-5-17

Test Laboratory: HUAWEI SAR/HAC Lab

HAC_ER3DV6_H210C-CDMA BC0-RC3 SO55-777CH

DUT: H210C; Type: cdma2000 Mobile Phone; Serial: SAR1

Communication System: HW-CDMA 2000; Frequency: 848.31 MHz;Duty Cycle: 1:1
Medium parameters used: σ = 0 S/m, ε_r = 1; ρ = 0 kg/m^3
Phantom section: RF Section

DASY Configuration:

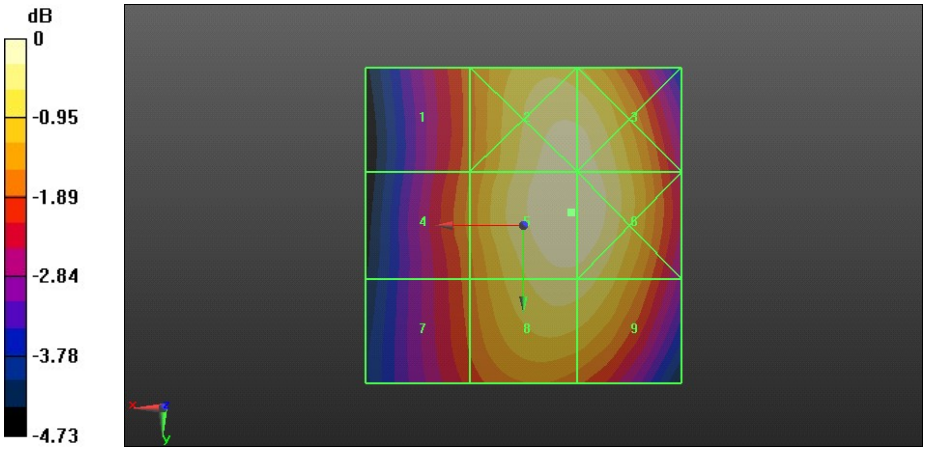
- Probe: ER3DV6 - SN2441; ConvF(1, 1, 1); Calibrated: 2012-11-26;
- Sensor-Surface: (Fix Surface), z = 8.7
- Electronics: DAE4 Sn852; Calibrated: 2012-11-22
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.4(1052); SEMCAD X 14.6.8(7028)

Device E-Field measurement (E-field scan for ANSI C63.19-2007 compliance)/E Scan - ER3D: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1): Interpolated grid: dx=0.5000 mm, dy=0.5000 mm
Device Reference Point: 0, 0, -6.3 mm
Reference Value = 106.8 V/m; Power Drift = -0.00 dB
PMF = 1.050 is applied.
E-field emissions = 88.82 V/m
Near-field category: M4 (AWF 0 dB)

PMF scaled E-field

Grid 1 **M4** **73.70 V/m**	Grid 2 **M4** **87.94 V/m**	Grid 3 **M4** **87.75 V/m**
Grid 4 **M4** **75.13 V/m**	Grid 5 **M4** **88.82 V/m**	Grid 6 **M4** **88.73 V/m**
Grid 7 **M4** **73.13 V/m**	Grid 8 **M4** **84.73 V/m**	Grid 9 **M4** **84.49 V/m**

Cursor:
Total = 88.82 V/m
E Category: M4
Location: -7.5, -2, 8.7 mm



0 dB = 88.82 V/m = 38.97 dBV/m

Date: 2013-5-17

Test Laboratory: HUAWEI SAR/HAC Lab

HAC_ER3DV6_H210C-CDMA BC0-RC3 SO55-384CH

DUT: H210C; Type: cdma2000 Mobile Phone; Serial: SAR1

Communication System: HW-CDMA 2000; Frequency: 836.52 MHz;Duty Cycle: 1:1
Medium parameters used: σ = 0 S/m, ε_r = 1; ρ = 0 kg/m^3
Phantom section: RF Section

DASY Configuration:

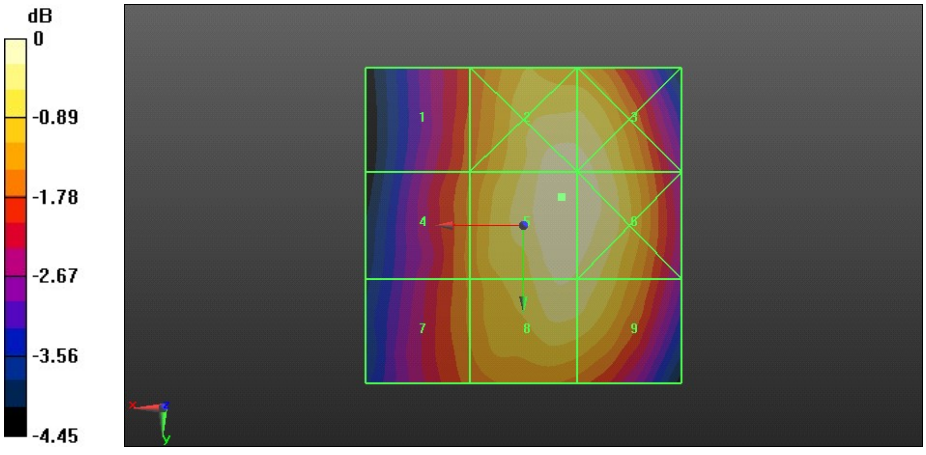
- Probe: ER3DV6 - SN2441; ConvF(1, 1, 1); Calibrated: 2012-11-26;
- Sensor-Surface: (Fix Surface), z = 8.7
- Electronics: DAE4 Sn852; Calibrated: 2012-11-22
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.4(1052); SEMCAD X 14.6.8(7028)

Device E-Field measurement (E-field scan for ANSI C63.19-2007 compliance)/E Scan - ER3D: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1): Interpolated grid: dx=0.5000 mm, dy=0.5000 mm
Device Reference Point: 0, 0, -6.3 mm
Reference Value = 97.96 V/m; Power Drift = 0.04 dB
PMF = 1.050 is applied.
E-field emissions = 80.71 V/m
Near-field category: M4 (AWF 0 dB)

PMF scaled E-field

Grid 1 **M4** **67.51 V/m**	Grid 2 **M4** **80.11 V/m**	Grid 3 **M4** **79.58 V/m**
Grid 4 **M4** **69.09 V/m**	Grid 5 **M4** **80.71 V/m**	Grid 6 **M4** **80.14 V/m**
Grid 7 **M4** **68.70 V/m**	Grid 8 **M4** **78.25 V/m**	Grid 9 **M4** **77.60 V/m**

Cursor:
Total = 80.71 V/m
E Category: M4
Location: -6, -4.5, 8.7 mm



0 dB = 80.71 V/m = 38.14 dBV/m

Date: 2013-5-17

Test Laboratory: HUAWEI SAR/HAC Lab

HAC_ER3DV6_H210C-CDMA BC0-RC3 SO55-1013CH

DUT: H210C; Type: cdma2000 Mobile Phone; Serial: SAR1

Communication System: HW-CDMA 2000; Frequency: 824.7 MHz;Duty Cycle: 1:1
Medium parameters used: σ = 0 S/m, ε_r = 1; ρ = 0 kg/m^3
Phantom section: RF Section

DASY Configuration:

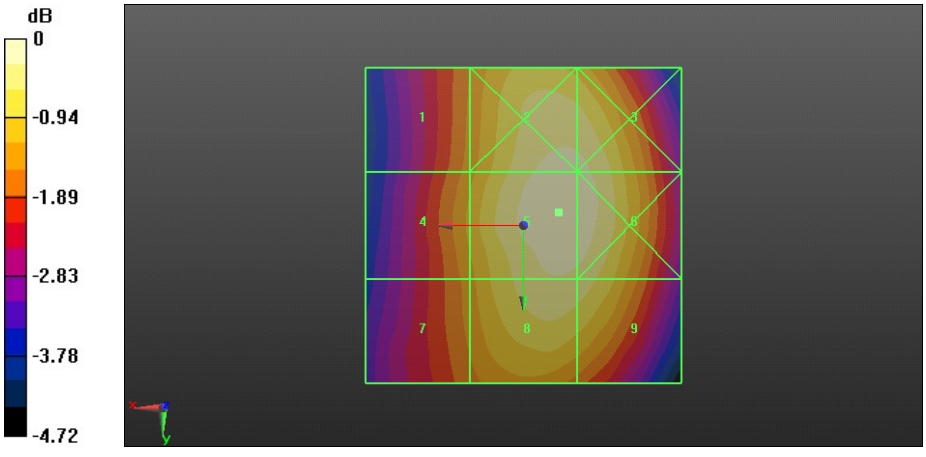
- Probe: ER3DV6 - SN2441; ConvF(1, 1, 1); Calibrated: 2012-11-26;
- Sensor-Surface: (Fix Surface), z = 8.7
- Electronics: DAE4 Sn852; Calibrated: 2012-11-22
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.4(1052); SEMCAD X 14.6.8(7028)

Device E-Field measurement (E-field scan for ANSI C63.19-2007 compliance)/E Scan - ER3D: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1): Interpolated grid: dx=0.5000 mm, dy=0.5000 mm
Device Reference Point: 0, 0, -6.3 mm
Reference Value = 97.14 V/m; Power Drift = -0.07 dB
PMF = 1.050 is applied.
E-field emissions = 79.49 V/m
Near-field category: M4 (AWF 0 dB)

PMF scaled E-field

Grid 1 **M4** **67.81 V/m**	Grid 2 **M4** **77.93 V/m**	Grid 3 **M4** **77.77 V/m**
Grid 4 **M4** **69.49 V/m**	Grid 5 **M4** **79.49 V/m**	Grid 6 **M4** **78.91 V/m**
Grid 7 **M4** **67.87 V/m**	Grid 8 **M4** **76.45 V/m**	Grid 9 **M4** **75.83 V/m**

Cursor:
Total = 79.49 V/m
E Category: M4
Location: -5.5, -2, 8.7 mm



0 dB = 79.49 V/m = 38.01 dBV/m

Date: 2013-5-17

Test Laboratory: HUAWEI SAR/HAC Lab

HAC_ER3DV6_H210C-CDMA BC0-RC3 SO55-777CH with battery 2#

DUT: H210C; Type: cdma2000 Mobile Phone; Serial: SAR1

Communication System: HW-CDMA 2000; Frequency: 848.31 MHz;Duty Cycle: 1:1
Medium parameters used: σ = 0 S/m, ε_r = 1; ρ = 0 kg/m^3
Phantom section: RF Section

DASY Configuration:

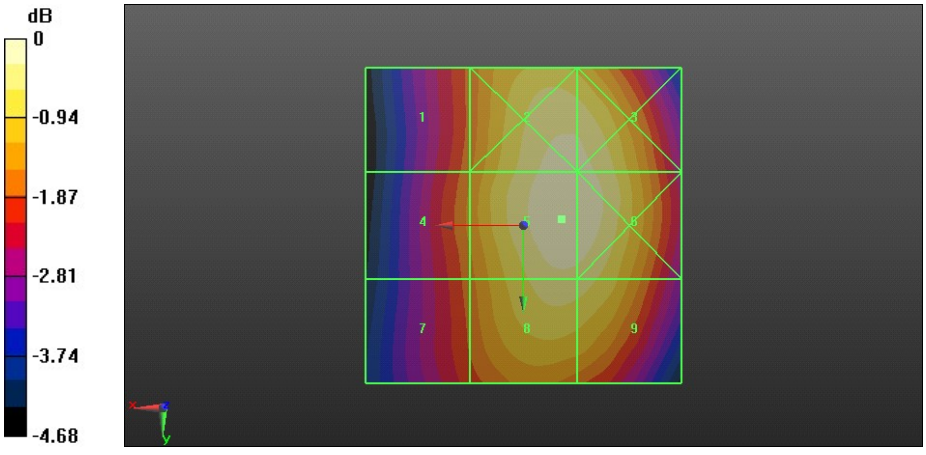
- Probe: ER3DV6 - SN2441; ConvF(1, 1, 1); Calibrated: 2012-11-26;
- Sensor-Surface: (Fix Surface), z = 8.7
- Electronics: DAE4 Sn852; Calibrated: 2012-11-22
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.4(1052); SEMCAD X 14.6.8(7028)

Device E-Field measurement (E-field scan for ANSI C63.19-2007 compliance)/E Scan - ER3D: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1): Interpolated grid: dx=0.5000 mm, dy=0.5000 mm
Device Reference Point: 0, 0, -6.3 mm
Reference Value = 107.2 V/m; Power Drift = -0.06 dB
PMF = 1.050 is applied.
E-field emissions = 88.73 V/m
Near-field category: M4 (AWF 0 dB)

PMF scaled E-field

Grid 1 **M4** **73.69 V/m**	Grid 2 **M4** **87.28 V/m**	Grid 3 **M4** **87.08 V/m**
Grid 4 **M4** **75.03 V/m**	Grid 5 **M4** **88.73 V/m**	Grid 6 **M4** **88.27 V/m**
Grid 7 **M4** **73.16 V/m**	Grid 8 **M4** **84.78 V/m**	Grid 9 **M4** **84.35 V/m**

Cursor:
Total = 88.73 V/m
E Category: M4
Location: -6, -1, 8.7 mm



0 dB = 88.73 V/m = 38.96 dBV/m

Date: 2013-5-17

Test Laboratory: HUAWEI SAR/HAC Lab

HAC_ER3DV6_H210C-CDMA BC1-RC3 SO55-1175CH

DUT: H210C; Type: cdma2000 Mobile Phone; Serial: SAR1

Communication System: HW-CDMA 2000; Frequency: 1908.75 MHz;Duty Cycle: 1:1
Medium parameters used: σ = 0 S/m, ε_r = 1; ρ = 0 kg/m^3
Phantom section: RF Section

DASY Configuration:

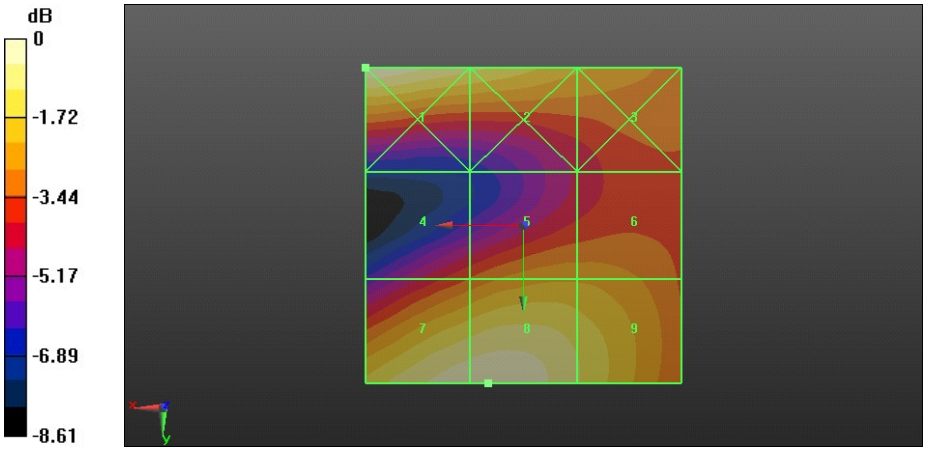
- Probe: ER3DV6 - SN2441; ConvF(1, 1, 1); Calibrated: 2012-11-26;
- Sensor-Surface: (Fix Surface), z = 8.7
- Electronics: DAE4 Sn852; Calibrated: 2012-11-22
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.4(1052); SEMCAD X 14.6.8(7028)

Device E-Field measurement (E-field scan for ANSI C63.19-2007 compliance)/E Scan - ER3D: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1): Interpolated grid: dx=0.5000 mm, dy=0.5000 mm
Device Reference Point: 0, 0, -6.3 mm
Reference Value = 22.54 V/m; Power Drift = -0.00 dB
PMF = 1.020 is applied.
E-field emissions = 38.19 V/m
Near-field category: M4 (AWF 0 dB)

PMF scaled E-field

Grid 1 **M4** **38.59 V/m**	Grid 2 **M4** **34.70 V/m**	Grid 3 **M4** **30.11 V/m**
Grid 4 **M4** **26.18 V/m**	Grid 5 **M4** **29.43 V/m**	Grid 6 **M4** **29.38 V/m**
Grid 7 **M4** **37.95 V/m**	Grid 8 **M4** **38.19 V/m**	Grid 9 **M4** **34.05 V/m**

Cursor:
Total = 38.59 V/m
E Category: M4
Location: 25, -25, 8.7 mm



0 dB = 38.59 V/m = 31.73 dBV/m

Date: 2013-5-17

Test Laboratory: HUAWEI SAR/HAC Lab

HAC_ER3DV6_H210C-CDMA BC1-RC3 SO55-600CH

DUT: H210C; Type: cdma2000 Mobile Phone; Serial: SAR1

Communication System: HW-CDMA 2000; Frequency: 1880 MHz;Duty Cycle: 1:1
Medium parameters used: $\sigma = 0$ S/m, $\varepsilon_r = 1$; $\rho = 0$ kg/m^3
Phantom section: RF Section

DASY Configuration:

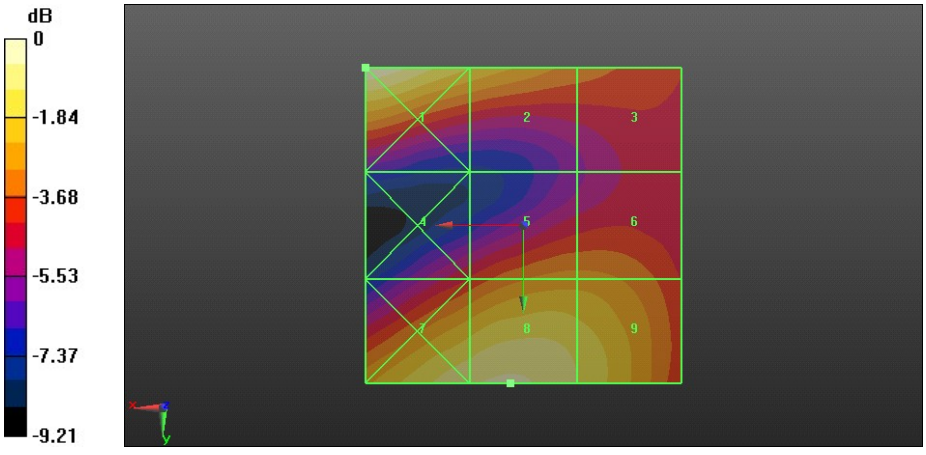
- Probe: ER3DV6 - SN2441; ConvF(1, 1, 1); Calibrated: 2012-11-26;
- Sensor-Surface: (Fix Surface), z = 8.7
- Electronics: DAE4 Sn852; Calibrated: 2012-11-22
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.4(1052); SEMCAD X 14.6.8(7028)

Device E-Field measurement (E-field scan for ANSI C63.19-2007 compliance)/E Scan - ER3D: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1): Interpolated grid: dx=0.5000 mm, dy=0.5000 mm
Device Reference Point: 0, 0, -6.3 mm
Reference Value = 22.38 V/m; Power Drift = 0.09 dB
PMF = 1.020 is applied.
E-field emissions = 39.32 V/m
Near-field category: M4 (AWF 0 dB)

PMF scaled E-field

Grid 1 **M4** **41.70 V/m**	Grid 2 **M4** **33.98 V/m**	Grid 3 **M4** **28.79 V/m**
Grid 4 **M4** **25.75 V/m**	Grid 5 **M4** **30.35 V/m**	Grid 6 **M4** **30.34 V/m**
Grid 7 **M4** **38.63 V/m**	Grid 8 **M4** **39.32 V/m**	Grid 9 **M4** **36.18 V/m**

Cursor:
Total = 41.70 V/m
E Category: M4
Location: 25, -25, 8.7 mm



0 dB = 41.70 V/m = 32.40 dBV/m

Date: 2013-5-17

Test Laboratory: HUAWEI SAR/HAC Lab

HAC_ER3DV6_H210C-CDMA BC1-RC3 SO55-25CH

DUT: H210C; Type: cdma2000 Mobile Phone; Serial: SAR1

Communication System: HW-CDMA 2000; Frequency: 1851.25 MHz;Duty Cycle: 1:1
Medium parameters used: σ = 0 S/m, ε_r = 1; ρ = 0 kg/m^3
Phantom section: RF Section

DASY Configuration:

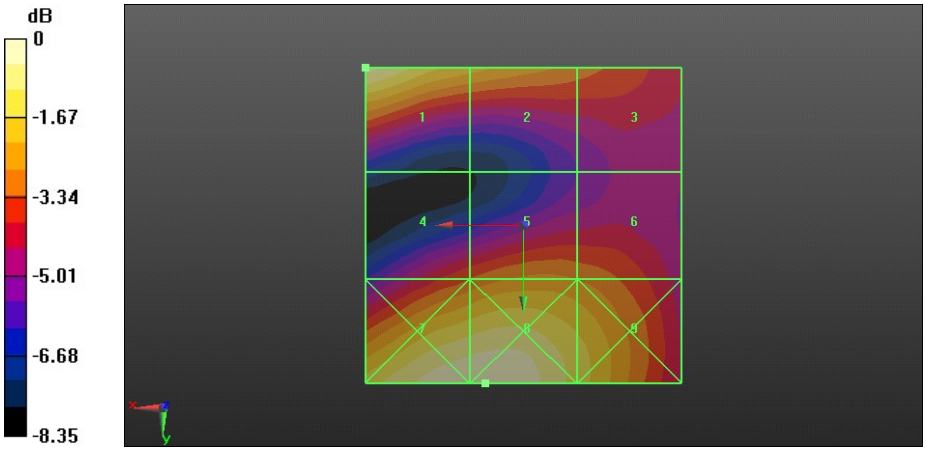
- Probe: ER3DV6 - SN2441; ConvF(1, 1, 1); Calibrated: 2012-11-26;
- Sensor-Surface: (Fix Surface), z = 8.7
- Electronics: DAE4 Sn852; Calibrated: 2012-11-22
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.4(1052); SEMCAD X 14.6.8(7028)

Device E-Field measurement (E-field scan for ANSI C63.19-2007 compliance)/E Scan - ER3D: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1): Interpolated grid: dx=0.5000 mm, dy=0.5000 mm
Device Reference Point: 0, 0, -6.3 mm
Reference Value = 22.74 V/m; Power Drift = -0.10 dB
PMF = 1.020 is applied.
E-field emissions = 37.12 V/m
Near-field category: M4 (AWF 0 dB)

PMF scaled E-field

Grid 1 **M4** **37.12 V/m**	Grid 2 **M4** **30.64 V/m**	Grid 3 **M4** **27.13 V/m**
Grid 4 **M4** **26.19 V/m**	Grid 5 **M4** **28.41 V/m**	Grid 6 **M4** **27.81 V/m**
Grid 7 **M4** **38.17 V/m**	Grid 8 **M4** **38.33 V/m**	Grid 9 **M4** **32.85 V/m**

Cursor:
Total = 38.33 V/m
E Category: M4
Location: 6, 25, 8.7 mm



0 dB = 38.33 V/m = 31.67 dBV/m

Date: 2013-5-17

Test Laboratory: HUAWEI SAR/HAC Lab

HAC_ER3DV6_H210C-CDMA BC1-RC3 SO55-600CH with battery 2#

DUT: H210C; Type: cdma2000 Mobile Phone; Serial: SAR1

Communication System: HW-CDMA 2000; Frequency: 1880 MHz;Duty Cycle: 1:1
Medium parameters used: σ = 0 S/m, ε_r = 1; ρ = 0 kg/m^3
Phantom section: RF Section

DASY Configuration:

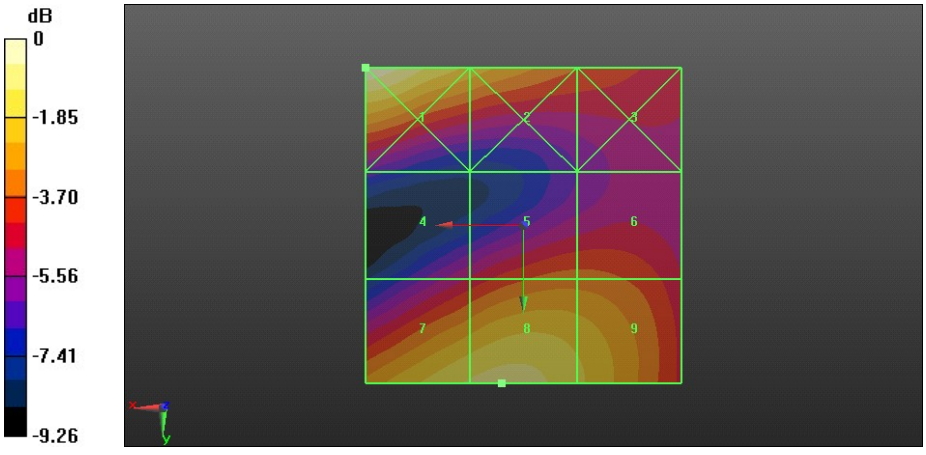
- Probe: ER3DV6 - SN2441; ConvF(1, 1, 1); Calibrated: 2012-11-26;
- Sensor-Surface: (Fix Surface), z = 8.7
- Electronics: DAE4 Sn852; Calibrated: 2012-11-22
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.4(1052); SEMCAD X 14.6.8(7028)

Device E-Field measurement (E-field scan for ANSI C63.19-2007 compliance)/E Scan - ER3D: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1): Interpolated grid: dx=0.5000 mm, dy=0.5000 mm
Device Reference Point: 0, 0, -6.3 mm
Reference Value = 20.43 V/m; Power Drift = -0.04 dB
PMF = 1.020 is applied.
E-field emissions = 36.97 V/m
Near-field category: M4 (AWF 0 dB)

PMF scaled E-field

Grid 1 **M4** **41.36 V/m**	Grid 2 **M4** **32.96 V/m**	Grid 3 **M4** **27.21 V/m**
Grid 4 **M4** **23.77 V/m**	Grid 5 **M4** **28.05 V/m**	Grid 6 **M4** **28.03 V/m**
Grid 7 **M4** **36.25 V/m**	Grid 8 **M4** **36.97 V/m**	Grid 9 **M4** **34.05 V/m**

Cursor:
Total = 41.36 V/m
E Category: M4
Location: 25, -25, 8.7 mm



0 dB = 41.36 V/m = 32.33 dBV/m

Date: 2013-5-17

Test Laboratory: HUAWEI SAR/HAC Lab

HAC_H3DV6_H210C-CDMA BC0-RC3 SO55-777CH

DUT: H210C; Type: cdma2000 Mobile Phone; Serial: SAR1

Communication System: HW-CDMA 2000; Frequency: 848.31 MHz;Duty Cycle: 1:1
Medium parameters used: σ = 0 S/m, ε_r = 1; ρ = 0 kg/m^3
Phantom section: RF Section

DASY Configuration:

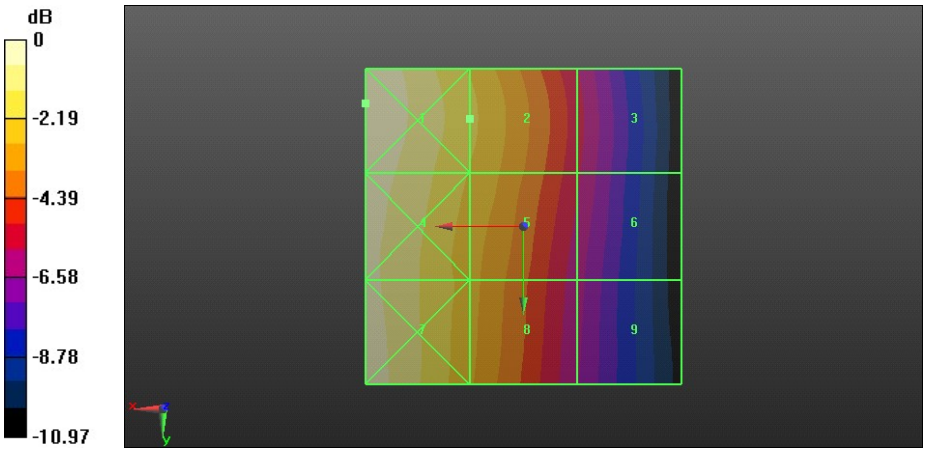
- Probe: H3DV6 - SN6270; ; Calibrated: 2012-11-26
- Sensor-Surface: (Fix Surface), z = 8.7
- Electronics: DAE4 Sn852; Calibrated: 2012-11-22
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.4(1052); SEMCAD X 14.6.8(7028)

Device H-Field measurement with H3DV6 probe (H-field scan for ANSI C63.19-2007 compliance)/H Scan - H3DV6: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1): Interpolated grid: dx=0.5000 mm, dy=0.5000 mm
Device Reference Point: 0, 0, -6.3 mm
Reference Value = 0.1500 A/m; Power Drift = -0.10 dB
PMF = 0.9900 is applied.
H-field emissions = 0.1710 A/m
Near-field category: M4 (AWF 0 dB)

PMF scaled H-field

Grid 1 **M4** **0.215 A/m**	Grid 2 **M4** **0.171 A/m**	Grid 3 **M4** **0.114 A/m**
Grid 4 **M4** **0.209 A/m**	Grid 5 **M4** **0.166 A/m**	Grid 6 **M4** **0.112 A/m**
Grid 7 **M4** **0.208 A/m**	Grid 8 **M4** **0.160 A/m**	Grid 9 **M4** **0.105 A/m**

Cursor:
Total = 0.2150 A/m
H Category: M4
Location: 25, -19.5, 8.7 mm



0 dB = 0.2150 A/m = -13.35 dBA/m

Date: 2013-5-17

Test Laboratory: HUAWEI SAR/HAC Lab

HAC_H3DV6_H210C-CDMA BC0-RC3 SO55-384CH

DUT: H210C; Type: cdma2000 Mobile Phone; Serial: SAR1

Communication System: HW-CDMA 2000; Frequency: 836.52 MHz;Duty Cycle: 1:1
Medium parameters used: σ = 0 S/m, ε_r = 1; ρ = 0 kg/m^3
Phantom section: RF Section

DASY Configuration:

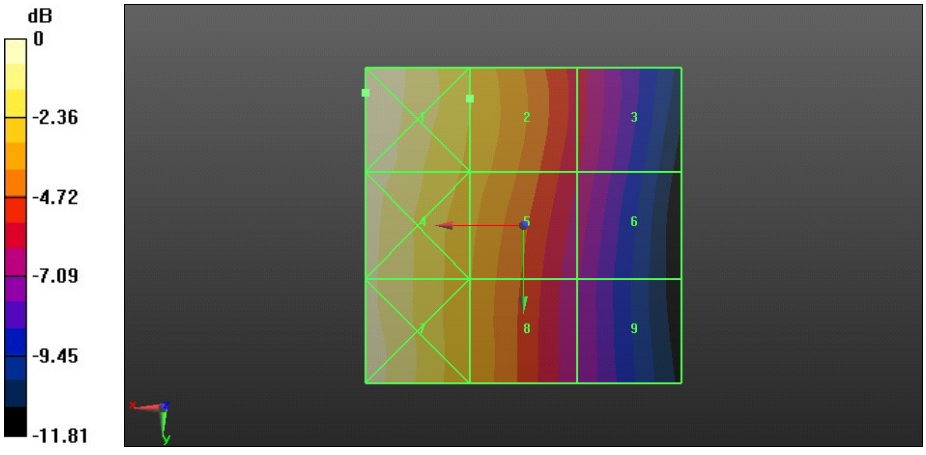
- Probe: H3DV6 - SN6270; ; Calibrated: 2012-11-26
- Sensor-Surface: (Fix Surface), z = 8.7
- Electronics: DAE4 Sn852; Calibrated: 2012-11-22
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.4(1052); SEMCAD X 14.6.8(7028)

Device H-Field measurement with H3DV6 probe (H-field scan for ANSI C63.19-2007 compliance)/H Scan - H3DV6: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1): Interpolated grid: dx=0.5000 mm, dy=0.5000 mm
Device Reference Point: 0, 0, -6.3 mm
Reference Value = 0.1220 A/m; Power Drift = -0.12 dB
PMF = 0.9900 is applied.
H-field emissions = 0.1433 A/m
Near-field category: M4 (AWF 0 dB)

PMF scaled H-field

Grid 1 **M4** **0.186 A/m**	Grid 2 **M4** **0.143 A/m**	Grid 3 **M4** **0.095 A/m**
Grid 4 **M4** **0.179 A/m**	Grid 5 **M4** **0.138 A/m**	Grid 6 **M4** **0.091 A/m**
Grid 7 **M4** **0.179 A/m**	Grid 8 **M4** **0.131 A/m**	Grid 9 **M4** **0.084 A/m**

Cursor:
Total = 0.1865 A/m
H Category: M4
Location: 25, -21, 8.7 mm



0 dB = 0.1865 A/m = -14.59 dBA/m

Date: 2013-5-17

Test Laboratory: HUAWEI SAR/HAC Lab

HAC_H3DV6_H210C-CDMA BC0-RC3 SO55-1013CH

DUT: H210C; Type: cdma2000 Mobile Phone; Serial: SAR1

Communication System: HW-CDMA 2000; Frequency: 824.7 MHz;Duty Cycle: 1:1
Medium parameters used: σ = 0 S/m, ε_r = 1; ρ = 0 kg/m^3
Phantom section: RF Section

DASY Configuration:

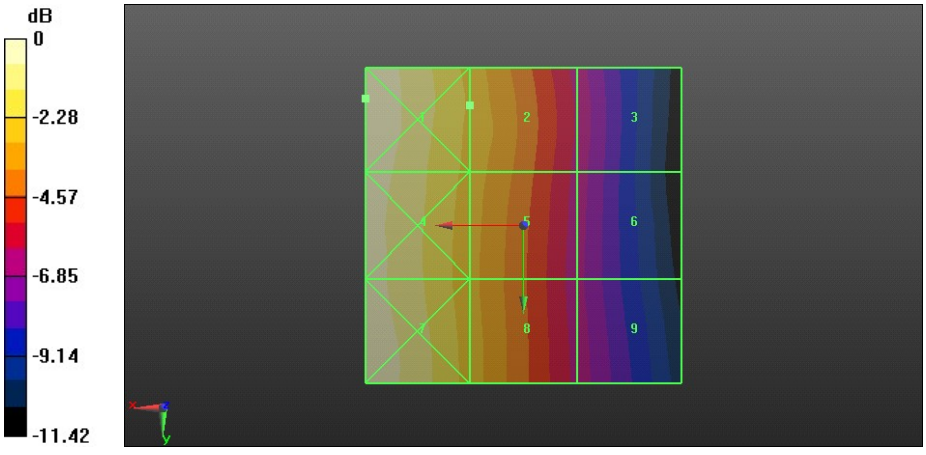
- Probe: H3DV6 - SN6270; ; Calibrated: 2012-11-26
- Sensor-Surface: (Fix Surface), z = 8.7
- Electronics: DAE4 Sn852; Calibrated: 2012-11-22
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.4(1052); SEMCAD X 14.6.8(7028)

Device H-Field measurement with H3DV6 probe (H-field scan for ANSI C63.19-2007 compliance)/H Scan - H3DV6: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1): Interpolated grid: dx=0.5000 mm, dy=0.5000 mm
Device Reference Point: 0, 0, -6.3 mm
Reference Value = 0.1130 A/m; Power Drift = -0.04 dB
PMF = 0.9900 is applied.
H-field emissions = 0.1316 A/m
Near-field category: M4 (AWF 0 dB)

PMF scaled H-field

Grid 1 **M4** **0.173 A/m**	Grid 2 **M4** **0.132 A/m**	Grid 3 **M4** **0.085 A/m**
Grid 4 **M4** **0.168 A/m**	Grid 5 **M4** **0.129 A/m**	Grid 6 **M4** **0.084 A/m**
Grid 7 **M4** **0.173 A/m**	Grid 8 **M4** **0.129 A/m**	Grid 9 **M4** **0.084 A/m**

Cursor:
Total = 0.1735 A/m
H Category: M4
Location: 25, -20, 8.7 mm



0 dB = 0.1735 A/m = -15.22 dBA/m

Date: 2013-5-17

Test Laboratory: HUAWEI SAR/HAC Lab

HAC_H3DV6_H210C-CDMA BC0-RC3 SO55-777CH with battery 2#

DUT: H210C; Type: cdma2000 Mobile Phone; Serial: SAR1

Communication System: HW-CDMA 2000; Frequency: 848.31 MHz;Duty Cycle: 1:1
Medium parameters used: σ = 0 S/m, ε_r = 1; ρ = 0 kg/m^3
Phantom section: RF Section

DASY Configuration:

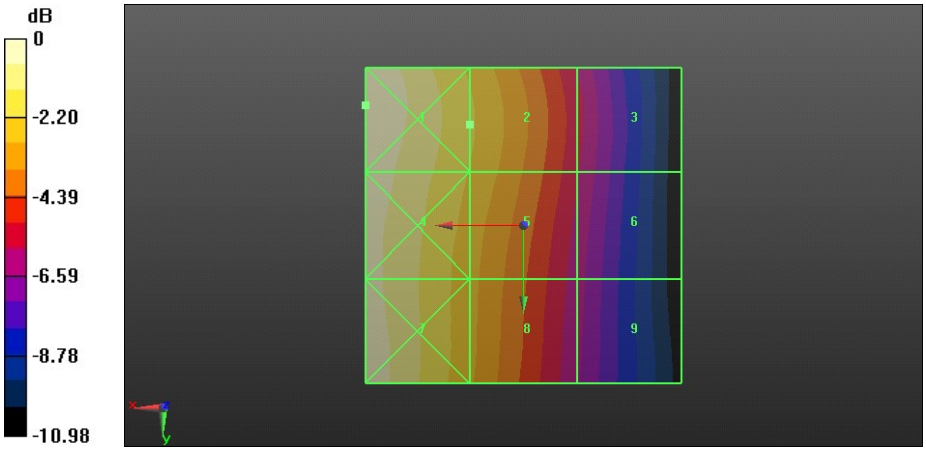
- Probe: H3DV6 - SN6270; ; Calibrated: 2012-11-26
- Sensor-Surface: (Fix Surface), z = 8.7
- Electronics: DAE4 Sn852; Calibrated: 2012-11-22
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.4(1052); SEMCAD X 14.6.8(7028)

Device H-Field measurement with H3DV6 probe (H-field scan for ANSI C63.19-2007 compliance)/H Scan - H3DV6: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1): Interpolated grid: dx=0.5000 mm, dy=0.5000 mm
Device Reference Point: 0, 0, -6.3 mm
Reference Value = 0.1440 A/m; Power Drift = 0.02 dB
PMF = 0.9900 is applied.
H-field emissions = 0.1647 A/m
Near-field category: M4 (AWF 0 dB)

PMF scaled H-field

Grid 1 **M4** **0.209 A/m**	Grid 2 **M4** **0.165 A/m**	Grid 3 **M4** **0.110 A/m**
Grid 4 **M4** **0.203 A/m**	Grid 5 **M4** **0.162 A/m**	Grid 6 **M4** **0.108 A/m**
Grid 7 **M4** **0.203 A/m**	Grid 8 **M4** **0.154 A/m**	Grid 9 **M4** **0.102 A/m**

Cursor:
Total = 0.2088 A/m
H Category: M4
Location: 25, -19, 8.7 mm



0 dB = 0.2088 A/m = -13.61 dBA/m

Date: 2013-5-17

Test Laboratory: HUAWEI SAR/HAC Lab

HAC_H3DV6_H210C-CDMA BC1-RC3 SO55-1175CH

DUT: H210C; Type: cdma2000 Mobile Phone; Serial: SAR1

Communication System: HW-CDMA 2000; Frequency: 1908.75 MHz;Duty Cycle: 1:1
Medium parameters used: σ = 0 S/m, ε_r = 1; ρ = 0 kg/m^3
Phantom section: RF Section

DASY Configuration:

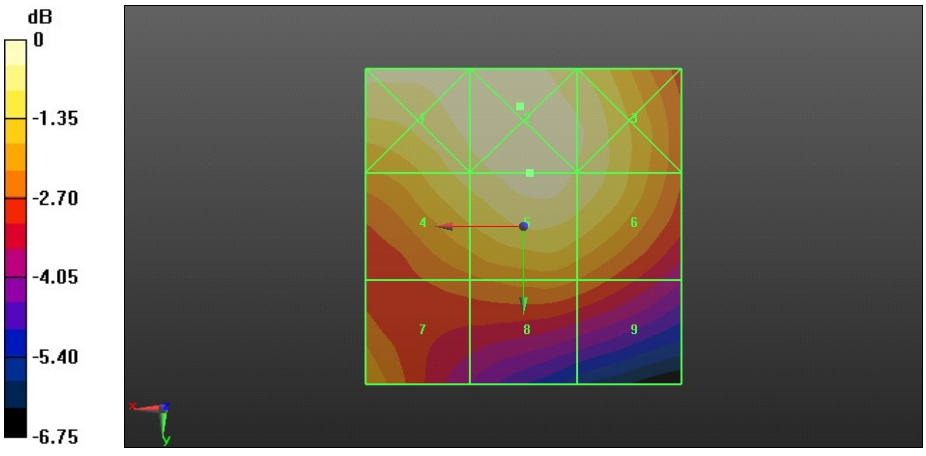
- Probe: H3DV6 - SN6270; ; Calibrated: 2012-11-26
- Sensor-Surface: (Fix Surface), z = 8.7
- Electronics: DAE4 Sn852; Calibrated: 2012-11-22
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.4(1052); SEMCAD X 14.6.8(7028)

Device H-Field measurement with H3DV6 probe (H-field scan for ANSI C63.19-2007 compliance)/H Scan - H3DV6: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1): Interpolated grid: dx=0.5000 mm, dy=0.5000 mm
Device Reference Point: 0, 0, -6.3 mm
Reference Value = 0.1080 A/m; Power Drift = 0.11 dB
PMF = 0.9400 is applied.
H-field emissions = 0.09971 A/m
Near-field category: M4 (AWF 0 dB)

PMF scaled H-field

Grid 1 **M4** **0.099 A/m**	Grid 2 **M4** **0.102 A/m**	Grid 3 **M4** **0.098 A/m**
Grid 4 **M4** **0.094 A/m**	Grid 5 **M4** **0.100 A/m**	Grid 6 **M4** **0.096 A/m**
Grid 7 **M4** **0.084 A/m**	Grid 8 **M4** **0.081 A/m**	Grid 9 **M4** **0.079 A/m**

Cursor:
Total = 0.1021 A/m
H Category: M4
Location: 0.5, -19, 8.7 mm



0 dB = 0.1021 A/m = -19.82 dBA/m

Date: 2013-5-17

Test Laboratory: HUAWEI SAR/HAC Lab

HAC_H3DV6_H210C-CDMA BC1-RC3 SO55-600CH

DUT: H210C; Type: cdma2000 Mobile Phone; Serial: SAR1

Communication System: HW-CDMA 2000; Frequency: 1880 MHz;Duty Cycle: 1:1
Medium parameters used: $\sigma = 0$ S/m, $\varepsilon_r = 1$; $\rho = 0$ kg/m^3
Phantom section: RF Section

DASY Configuration:

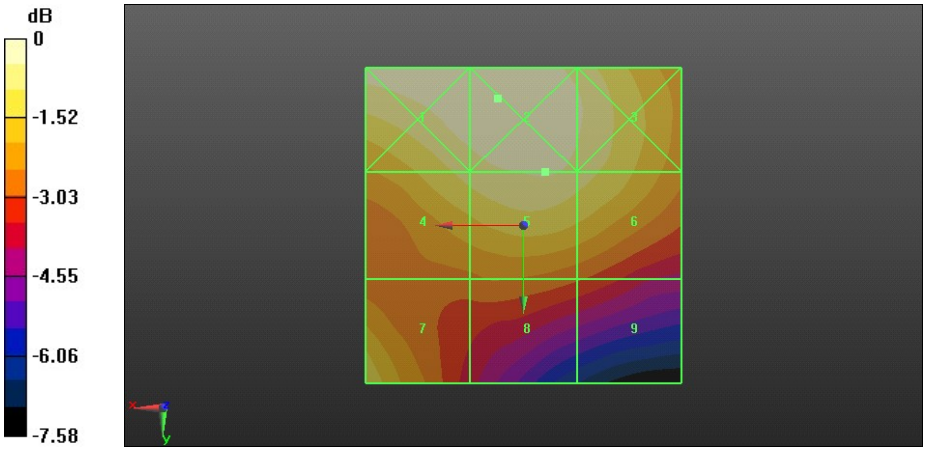
- Probe: H3DV6 - SN6270; ; Calibrated: 2012-11-26
- Sensor-Surface: (Fix Surface), z = 8.7
- Electronics: DAE4 Sn852; Calibrated: 2012-11-22
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.4(1052); SEMCAD X 14.6.8(7028)

Device H-Field measurement with H3DV6 probe (H-field scan for ANSI C63.19-2007 compliance)/H Scan - H3DV6: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1): Interpolated grid: dx=0.5000 mm, dy=0.5000 mm
Device Reference Point: 0, 0, -6.3 mm
Reference Value = 0.09800 A/m; Power Drift = 0.14 dB
PMF = 0.9400 is applied.
H-field emissions = 0.09258 A/m
Near-field category: M4 (AWF 0 dB)

PMF scaled H-field

Grid 1 **M4** **0.096 A/m**	Grid 2 **M4** **0.097 A/m**	Grid 3 **M4** **0.093 A/m**
Grid 4 **M4** **0.089 A/m**	Grid 5 **M4** **0.093 A/m**	Grid 6 **M4** **0.089 A/m**
Grid 7 **M4** **0.087 A/m**	Grid 8 **M4** **0.073 A/m**	Grid 9 **M4** **0.069 A/m**

Cursor:
Total = 0.09732 A/m
H Category: M4
Location: 4, -20, 8.7 mm



0 dB = 0.09732 A/m = -20.24 dBA/m

Date: 2013-5-17

Test Laboratory: HUAWEI SAR/HAC Lab

HAC_H3DV6_H210C-CDMA BC1-RC3 SO55-25CH

DUT: H210C; Type: cdma2000 Mobile Phone; Serial: SAR1

Communication System: HW-CDMA 2000; Frequency: 1851.25 MHz;Duty Cycle: 1:1
Medium parameters used: σ = 0 S/m, ε_r = 1; ρ = 0 kg/m^3
Phantom section: RF Section

DASY Configuration:

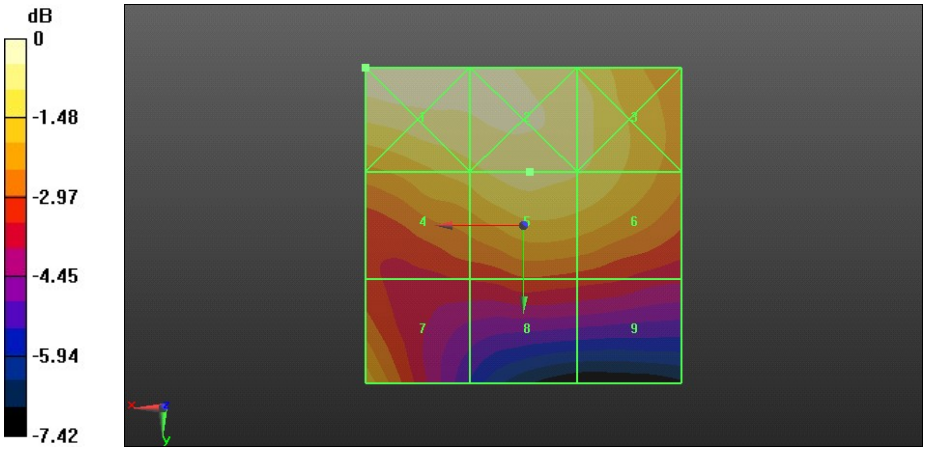
- Probe: H3DV6 - SN6270; ; Calibrated: 2012-11-26
- Sensor-Surface: (Fix Surface), z = 8.7
- Electronics: DAE4 Sn852; Calibrated: 2012-11-22
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.4(1052); SEMCAD X 14.6.8(7028)

Device H-Field measurement with H3DV6 probe (H-field scan for ANSI C63.19-2007 compliance)/H Scan - H3DV6: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1): Interpolated grid: dx=0.5000 mm, dy=0.5000 mm
Device Reference Point: 0, 0, -6.3 mm
Reference Value = 0.09600 A/m; Power Drift = -0.06 dB
PMF = 0.9400 is applied.
H-field emissions = 0.08866 A/m
Near-field category: M4 (AWF 0 dB)

PMF scaled H-field

Grid 1 **M4** **0.097 A/m**	Grid 2 **M4** **0.094 A/m**	Grid 3 **M4** **0.089 A/m**
Grid 4 **M4** **0.084 A/m**	Grid 5 **M4** **0.089 A/m**	Grid 6 **M4** **0.087 A/m**
Grid 7 **M4** **0.081 A/m**	Grid 8 **M4** **0.068 A/m**	Grid 9 **M4** **0.067 A/m**

Cursor:
Total = 0.09680 A/m
H Category: M4
Location: 25, -25, 8.7 mm



0 dB = 0.09680 A/m = -20.28 dBA/m

Date: 2013-5-17

Test Laboratory: HUAWEI SAR/HAC Lab

HAC_H3DV6_H210C-CDMA BC1-RC3 SO55-1175CH with battery 2#

DUT: H210C; Type: cdma2000 Mobile Phone; Serial: SAR1

Communication System: HW-CDMA 2000; Frequency: 1908.75 MHz;Duty Cycle: 1:1
Medium parameters used: σ = 0 S/m, ε_r = 1; ρ = 0 kg/m^3
Phantom section: RF Section

DASY Configuration:

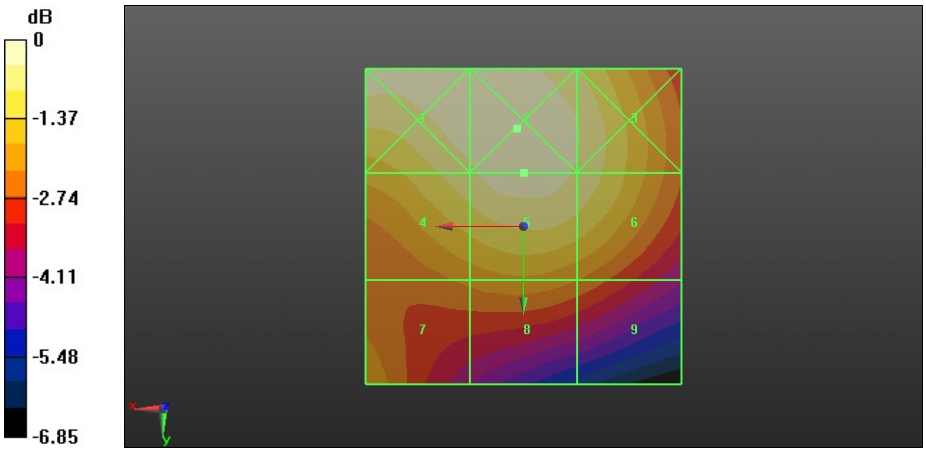
- Probe: H3DV6 - SN6270; ; Calibrated: 2012-11-26
- Sensor-Surface: (Fix Surface), z = 8.7
- Electronics: DAE4 Sn852; Calibrated: 2012-11-22
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.4(1052); SEMCAD X 14.6.8(7028)

Device H-Field measurement with H3DV6 probe (H-field scan for ANSI C63.19-2007 compliance)/H Scan - H3DV6: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1): Interpolated grid: dx=0.5000 mm, dy=0.5000 mm
Device Reference Point: 0, 0, -6.3 mm
Reference Value = 0.1100 A/m; Power Drift = 0.00 dB
PMF = 0.9400 is applied.
H-field emissions = 0.1015 A/m
Near-field category: M4 (AWF 0 dB)

PMF scaled H-field

Grid 1 **M4** **0.101 A/m**	Grid 2 **M4** **0.104 A/m**	Grid 3 **M4** **0.099 A/m**
Grid 4 **M4** **0.097 A/m**	Grid 5 **M4** **0.101 A/m**	Grid 6 **M4** **0.097 A/m**
Grid 7 **M4** **0.085 A/m**	Grid 8 **M4** **0.083 A/m**	Grid 9 **M4** **0.080 A/m**

Cursor:
Total = 0.1036 A/m
H Category: M4
Location: 1, -15.5, 8.7 mm



0 dB = 0.1036 A/m = -19.69 dBA/m